L Number	Hits	Search Text	DB	Time stamp
1	6	"6180995"	USPAT;	2004/09/07 07:02
-		0100773	US-PGPUB:	2001,03,07
			EPO; JPO	
2	9	"6307247"	USPAT;	2004/09/07 07:03
			US-PGPUB;	
			EPO; JPO	
3	13	"6287979"	USPAT;	2004/09/07 07:03
			US-PGPUB;	1
			EPO; JPO	
4	16	"4634494"	USPAT;	2004/09/07 07:03
			US-PGPUB;	
-		WE 740001 #	EPO; JPO	
5	19	"5742091"	USPAT;	2004/09/07 07:03
			US-PGPUB;	
6	16	"6303423"	EPO; JPO USPAT;	2004/09/07 07:03
"	1	0303423	US-PGPUB;	2004/09/07 07:03
			EPO; JPO	
7	72	"6180995" "6307247" "6287979" "4634494"	USPAT;	2004/09/07 07:04
'	'-	"5742091" "6303423"	US-PGPUB;	2004,03,07 07.04
		000010	EPO; JPO	
8	39	inductor and (oxide adj layer) and	USPAT;	2004/09/07 07:15
		("low-k" adj dielectric)	US-PGPUB;	'35,55 323
			EPO; JPO	
10	3	(inductor and (oxide adj layer) and	USPAT;	2004/09/07 07:15
		("low-k" adj dielectric)) and (air adj	US-PGPUB;	
		gap)	EPO; JPO	
9	39	(inductor and (oxide adj layer) and	USPAT;	2004/09/07 07:06
		("low-k" adj dielectric)) and (method	US-PGPUB;	
		process)	EPO; JPO	
11	120	inductor and oxide and ("low-k" near1	USPAT;	2004/09/07 07:15
1		(insulation dielectric))	US-PGPUB;	
1,0	,,,	(industrum and suids and (12 st. htt seems	EPO; JPO	/ /
12	17	(inductor and oxide and ("low-k" nearl	USPAT;	2004/09/07 07:15
		(insulation dielectric))) and (air adj gap)	US-PGPUB;	
13	0	inductor and (oxide with ("low-k" nearl	EPO; JPO USPAT;	2004/09/07 07:17
		(insulation dielectric)) with (air adj	US-PGPUB;	2004/03/07 07.17
		gap))	EPO; JPO	
14	o	inductor and (oxide with "low-k" with	USPAT:	2004/09/07 07:18
		(air adj gap))	US-PGPUB;	,,
			EPO; JPO	
15	0	inductor and (oxide near1 layer) and	USPAT;	2004/09/07 07:19
		("low-k" with (air adj gap))	US-PGPUB;	·
			EPO; JPO	
16	31	inductor and (oxide near1 layer) and	USPAT;	2004/09/07 07:19
		(("low-k" dielectric) with (air adj gap))	US-PGPUB;	
, ,	-	6405000 UPDW	EPO; JPO	
17	0	6495903.URPN.	USPAT	2004/09/07 07:23
18	8	("5539241" "5831331" "6153489" "6180433" "6231737" "6242781"	USPAT	2004/09/07 07:23
		"6180433" "6221727" "6242791" "6274920" "6287931").PN.		
19	67	("6180995" "6307247" "6287979" "4634494"	USPAT;	2004/09/07 08:19
~ ′	"	"5742091" "6303423") not ((inductor and	US-PGPUB;	2004/03/07 00:19
		(oxide adj layer) and ("low-k" adj	EPO; JPO	1
		dielectric)) and (method process)) not	Bro, Gro	
		((inductor and oxide and ("low-k" near1	1	
		(insulation dielectric))) and (air adj		
		gap)) not (inductor and (oxide near1		
		layer) and (("low-k" dielectric) with (air	1	
		adj gap)))		
20	17	"6413827"	USPAT;	2004/09/07 08:19
			US-PGPUB;	
			EPO; JPO	
21	0	6413827.pn. and inductor	USPAT;	2004/09/07 08:20
			US-PGPUB;	
			EPO; JPO	
22	0	"sc12765tp"	USPAT;	2004/09/07 09:30
			US-PGPUB;	
			EPO; JPO	

23	1 14	1 (law add le add dialogueig) with	TIODAM.	2004/09/07 09:37
23	14	, ,	USPAT;	2004/09/07 09:37
		(semiconductor adj fabrication adj process)	US-PGPUB; EPO; JPO	
24	0564763	1 •		2004/00/07 00 30
24	8564763	US -6,486,061 B1	USPAT;	2004/09/07 09:38
		US -6,472,325 B1	US-PGPUB;	
		US -6,465,372 B1	EPO; JPO	
		US -6,455,443 B1		
		US -6,440,878 B1		ĺ
		US -6,383,913 B1	ì	
	•	US -6,348,407 B1		
		US -6,331,420 B1		
		US -6,303,525 B1		
		US -6,197,704 B1		
		US -6,153,512		
25	11	6486061.pn.	USPAT;	2004/09/07 09:47
		6472325.pn.	US-PGPUB;	
		6465372.pn.	EPO; JPO	1
		6455443.pn.		
		6440878.pn.		
		6383913.pn.		
		6348407.pn.		
		6331420.pn.		
		6303525.pn.		
		6197704.pn.		
		6153512.pn.		
26	0	(substrate wafer) with (second near2 (low	USPAT;	2004/09/07 09:50
		adj k)) with void with polish\$3	US-PGPUB;	
		•	EPO; JPO	
27	1	(substrate wafer) with (low adj "k") with	USPAT;	2004/09/07 09:52
		void with polish\$3	US-PGPUB;	
	1	•	EPO; JPO	
28	1	(substrate wafer) with (low adj "k") with	USPAT;	2004/09/07 09:52
		(void (via adj hole)) with polish\$3	US-PGPUB;	
		, , , , , , , , , , , , , , , , , , ,	EPO; JPO	
29	11	(substrate wafer) with (low adj "k") with	USPAT;	2004/09/07 10:10
		(void via hole) with polish\$3	US-PGPUB;	2001,05,0. 20120
		(veste vas dese, when person, e	EPO; JPO	
30	8	((substrate wafer) with (low adj "k") with	USPAT;	2004/09/07 10:11
-		(void via hole) with polish\$3) and cvd	US-PGPUB;	=====================================
	1	,	EPO; JPO	
31	8	(((substrate wafer) with (low adj "k")	USPAT;	2004/09/07 10:11
_		with (void via hole) with polish\$3) and	US-PGPUB;	2001, 00, 0, 10.11
		cvd) and cmp	EPO; JPO	
	<u> </u>	1 Cra, and emp	I BEO, OPO	1